

FDP7045L/FDB7045L

N-Channel Logic Level PowerTrench® MOSFET

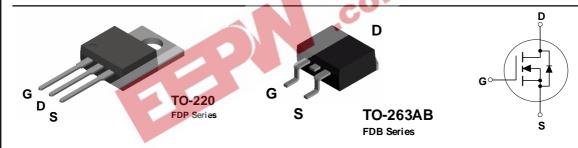
General Description

This N-Channel Logic Level MOSFET has been designed specifically to improve the overall efficiency of DC/DC converters using either synchronous or conventional switching PWM controllers.

These MOSFETs feature faster switching and lower gate charge than other MOSFETs with comparable $R_{\scriptscriptstyle DS(on)}$ specifications resulting in DC/DC power supply designs with higher overall efficiency.

Features

- 100 A, 30 V. $\begin{aligned} R_{\rm DS(ON)} &= 0.0045~\Omega \textcircled{0} V_{\rm GS} = 10~V \\ R_{\rm DS(ON)} &= 0.006~\Omega \textcircled{0} V_{\rm GS} = 4.5~V. \end{aligned}$
- Critical DC electrical parameters specified at elevated temperature.
- Rugged internal source-drain diode can eliminate the need for an external Zener diode transient suppressor.
- High performance PowerTrench technology for extremely low $R_{\text{DS(ON)}}$.
- 175°C maximum junction temperature rating.



Absolute Maximum Ratings T_C = 25°C unless otherwise noted

Symbol	Parameter		FDP7045L	FDB7045L	Units			
V _{DSS}	Drain-Source Voltage		3	V				
V_{GSS}	Gate-Source Voltage	±	20	V				
I _D	Maximum Drain Current - Continuous (N	Note 1)	1	00	Α			
			7	7 5				
	- Pulsed (N	Note 1)	3	00				
P _D	Total Power Dissipation @ T _C = 25°C		1	W				
	Derate above 25°C		0.	85	W/∘C			
T _J , T _{STG}	Operating and Storage Junction Temperature Ra	-65 to	∘C					
Thermal Characteristics								
$R_{\Theta^{JC}}$	Thermal Resistance, Junction-to-Case	1	∘C/W					
$R_{\Theta^{JA}}$	Thermal Resistance, Junction-to-Ambient		62	∘C/W				

Package Outlines and Ordering Information

Device Marking	Device	Reel Size	Tape Width	Quantity
FDB7045L	FDB7045L	13"	24mm	800
FDP7045L	FDP7045L	Tube	N/A	45

Symbol	Parameter	Test Conditions	Min	Тур	Max	Units
Off Char	acteristics					
BV _{DSS}	Drain-Source Breakdown Voltage	$V_{GS} = 0 \text{ V}, I_D = 250 \mu\text{A}$	30			V
<u>∆</u> BVdss ∆Tj	Breakdown Voltage Temperature Coefficient	I_D = 250 μ A, Referenced to 25°C		22		mV/∘C
I _{DSS}	Zero Gate Voltage Drain Current	$V_{DS} = 24 \text{ V}, V_{GS} = 0 \text{ V}$			1	μΑ
I _{GSSF}	Gate-Body Leakage Current, Forward	$V_{GS} = 20 \text{ V}, V_{DS} = 0 \text{ V}$			100	nA
I _{GSSR}	Gate-Body Leakage Current, Reverse	$V_{GS} = -20 \text{ V}, V_{DS} = 0 \text{ V}$			-100	nA
On Char	acteristics (Note 2)					
$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS} = V_{GS}, I_{D} = 250 \mu A$	1	1.5	3	V
<u>Δ</u> VGS(th) ΔΤ _J	Gate Threshold Voltage Temperature Coefficient	I _D = -250 μA, Referenced to 25°C		-5		mV/°C
R _{DS(on)}	Static Drain-Source On-Resistance	$V_{GS} = 10 \text{ V}, I_D = 50 \text{ A},$ $V_{GS} = 10 \text{ V}, I_D = 50 \text{ A}, T_J = 125 ^{\circ}\text{C}$ $V_{GS} = 4.5 \text{ V}, I_D = 40 \text{ A}$	18	0.0039 0.0056 0.0048	0.0045 0.0070 0.0060	Ω
I _{D(on)}	On-State Drain Current	$V_{GS} = 10 \text{ V}, V_{DS} = 10 \text{ V}$	50	-		Α
g _{FS}	Forward Transconductance	$V_{DS} = 5 \text{ V}, I_{D} = 50 \text{ A}$.1	120		S
Dynamic	: Characteristics	4 4 601				
C _{iss}	Input Capacitance	$V_{DS} = 15 \text{ V}, V_{GS} = 0 \text{ V},$		5400		pF
C _{oss}	Output Capacitance	f = 1.0 MHz		1170		pF
C _{rss}	Reverse Transfer Capacitance			530		pF
Switchin	g Characteristics (Note 2)					
t _{d(on)}	Turn-On Delay Time	$V_{DD} = 15 \text{ V}, I_D = 50 \text{ A},$		14	30	ns
t _r	Turn-On Rise Time	V _{GS} = 10 V		114	160	ns
t _{d(off)}	Turn-Off Delay Time			105	150	ns
t _f	Turn-Off Fall Time			115	160	ns
Q_g	Total Gate Charge	V _{DS} = 15 V,		50	70	nC
Q_{gs}	Gate-Source Charge	$I_D = 50 \text{ A}, V_{GS} = 5 \text{ V}$		16		nC
Q_{gd}	Gate-Drain Charge			16		nC
Drain-So	ource Diode Characteristics	and Maximum Ratings				
l _s	Maximum Continuous Drain-Source				75	Α
V _{SD}	Drain-Source Diode Forward	V = 0 V, I = 50 A (Note 2)		0.95	1.2	V

Notes:

1. Calculated continuous current based on maximum allowable junction temperature. Actual maximum continuous current limited by package constraints to 75A.

2. Pulse Test: Pulse Width ≤ 300 μs, Duty Cycle ≤ 2.0%

Typical Characteristics

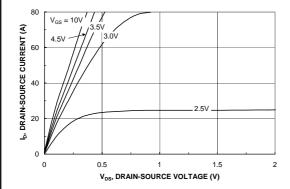


Figure 1. On-Region Characteristics.

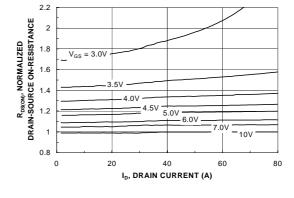


Figure 2. On-Resistance Variation with Drain Current and Gate Voltage.

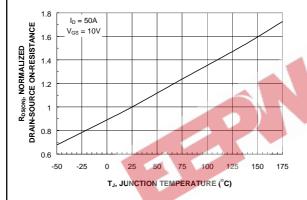


Figure 3. On-Resistance Variation with Temperature.

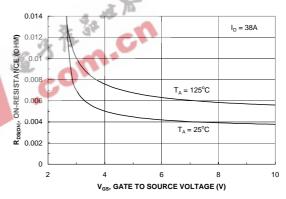


Figure 4. On-Resistance Variation with Gate-to-Source Voltage.

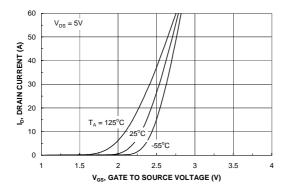


Figure 5. Transfer Characteristics.

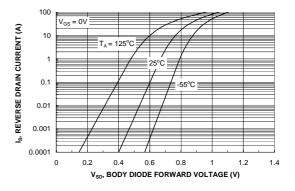
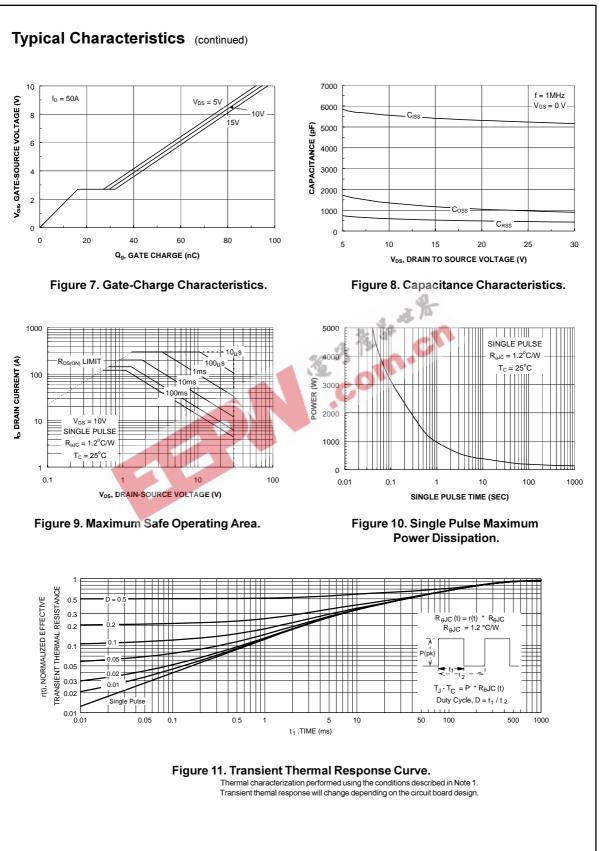
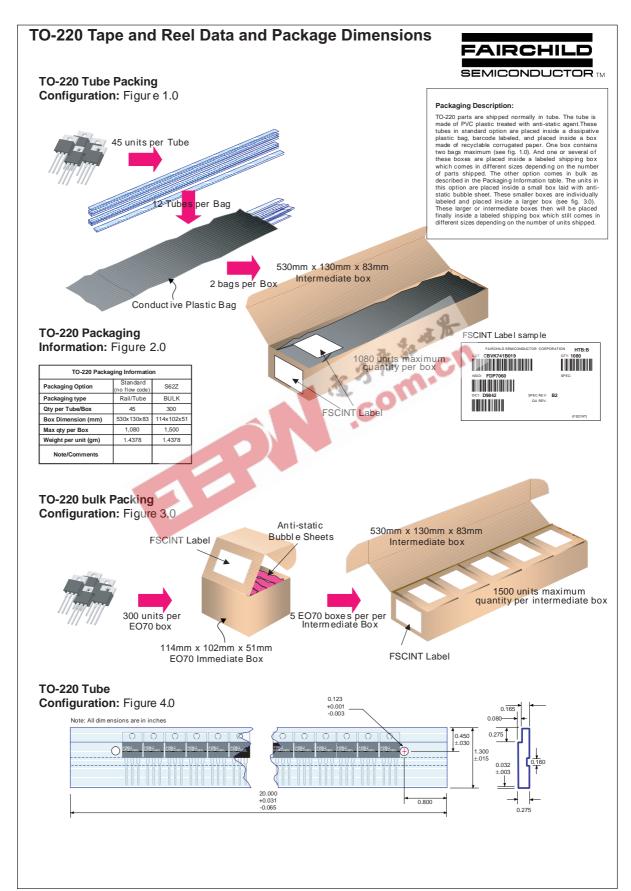
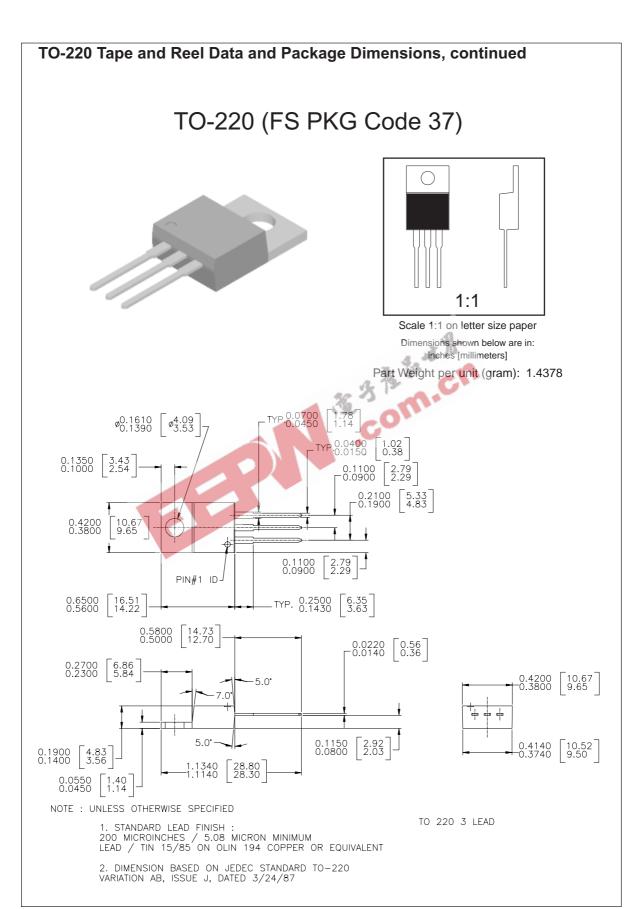
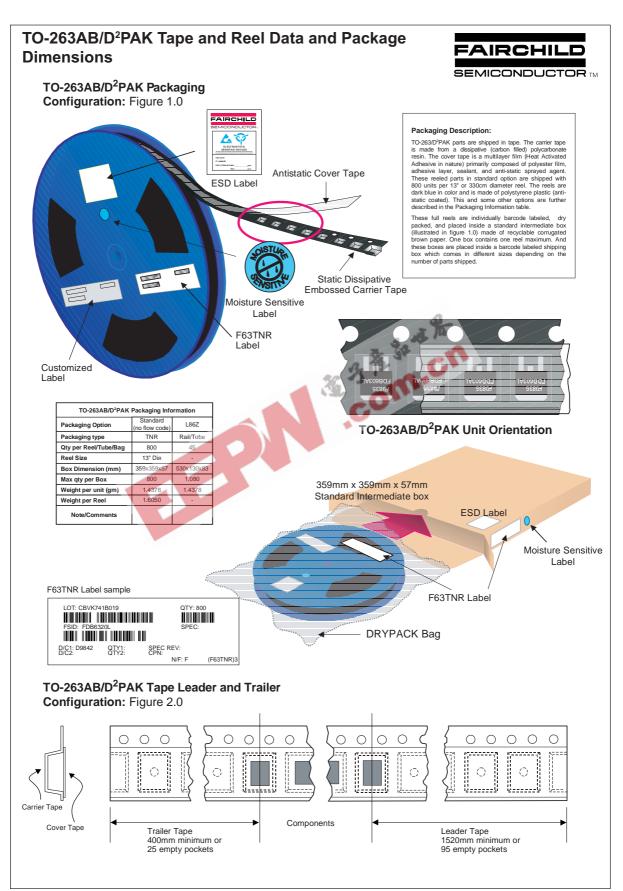


Figure 6. Body Diode Forward Voltage Variation with Source Current and Temperature.



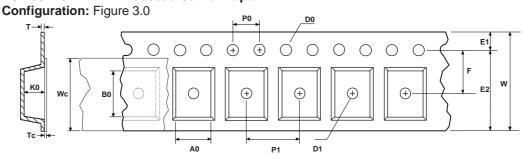






TO-263AB/D²PAK Tape and Reel Data and Package Dimensions, continued

TO-263AB/D²PAK Embossed Carrier Tape

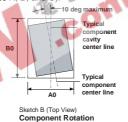




	Dimensions are in millimeter													
Pkg type	Α0	В0	w	D0	D1	E1	E2	F	P1	P0	K0	т	Wc	Тс
TO263AB/ D²PAK (24mm)	10.60 +/-0.10	15.80 +/-0.10	24.0 +/-0.3	1.55 +/-0.05	1.60 +/-0.10	1.75 +/-0.10	22.25 min	11.50 +/-0.10	16.0 +/-0.1	4.0 +/-0.1	4.90 +/-0.10	0.450 +/-0.150	21.0 +/-0.3	0.06 +/-0.02

Notes: A0, B0, and K0 dimensions are determined with respect to the EIA/Jedec RS-481 rotational and lateral movement requirements (see sketches A, B, and C).





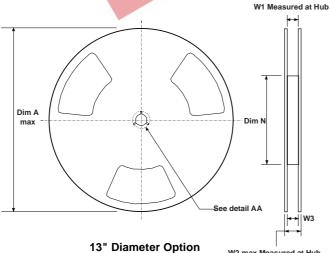


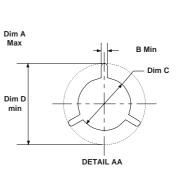
Sketch C (Top View)

Component lateral movement

TO-263AB/D²PAK Reel Configuration:

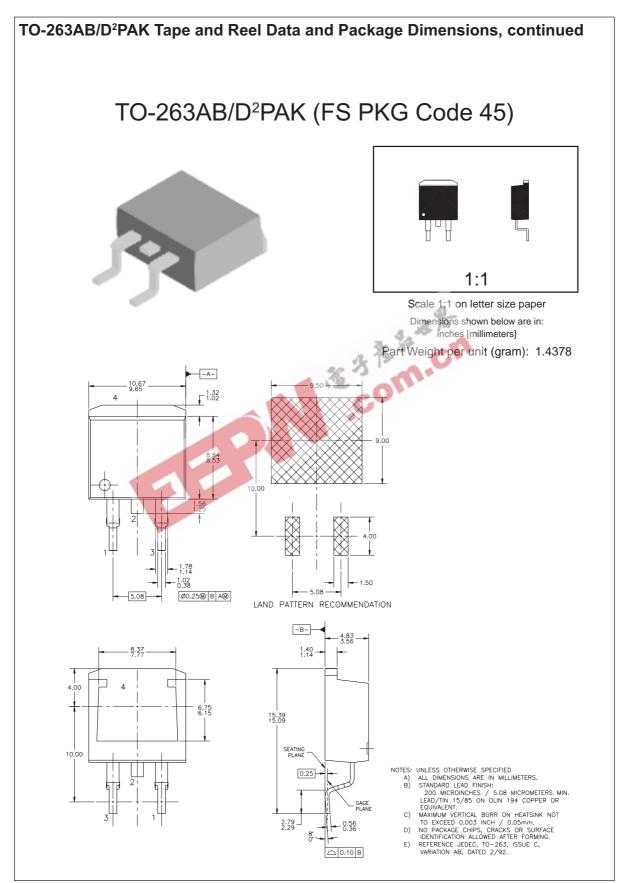
Figure 4.0





W2 max Measured at Hub

Dimensions are in inches and millimeters									
Tape Size	Reel Option	Dim A	Dim B	Dim C	Dim D	Dim N	Dim W1	Dim W2	Dim W3 (LSL-USL)
24mm	13" Dia	13.00 330	0.059 1.5	512 +0.020/-0.008 13 +0.5/-0.2	0.795 20.2	4.00 100	0.961 +0.078/-0.000 24.4 +2/0	1.197 30.4	0.941 - 0.1.079 23.9 - 27.4



TRADEMARKS

The following are registered and unregistered trademarks Fairchild Semiconductor owns or is authorized to use and is not intended to be an exhaustive list of all such trademarks.

FACT $^{\text{TM}}$ QFET $^{\text{TM}}$ FACT Quiet Series $^{\text{TM}}$ QS $^{\text{TM}}$

 $\begin{array}{lll} {\sf FAST}^{\circledcirc} & {\sf Quiet\ Series^{\sf TM}} \\ {\sf FASTr^{\sf TM}} & {\sf SuperSOT^{\sf TM}\text{--}3} \\ {\sf GTO^{\sf TM}} & {\sf SuperSOT^{\sf TM}\text{--}6} \\ {\sf HiSeC^{\sf TM}} & {\sf SuperSOT^{\sf TM}\text{--}8} \end{array}$

DISCLAIMER

FAIRCHILD SEMICONDUCTOR RESERVES THE RIGHT TO MAKE CHANGES WITHOUT FURTHER NOTICE TO ANY PRODUCTS HEREIN TO IMPROVE RELIABILITY, FUNCTION OR DESIGN. FAIRCHILD DOES NOT ASSUME ANY LIABILITY ARISING OUT OF THE APPLICATION OR USE OF ANY PRODUCT OR CIRCUIT DESCRIBED HEREIN; NEITHER DOES IT CONVEY ANY LICENSE UNDER ITS PATENT RIGHTS, NOR THE RIGHTS OF OTHERS.

LIFE SUPPORT POLICY

FAIRCHILD'S PRODUCTS ARE NOT AUTHORIZED FOR USE AS CRITICAL COMPONENTS IN LIFE SUPPORT DEVICES OR SYSTEMS WITHOUT THE EXPRESS WRITTEN APPROVAL OF FAIRCHILD SEMICONDUCTOR CORPORATION. As used herein:

1. Life support devices or systems are devices or systems which, (a) are intended for surgical implant into the body, or (b) support or sustain life, or (c) whose failure to perform when properly used in accordance with instructions for use provided in the labeling, can be reasonably expected to result in significant injury to the user.

 A critical component is any component of a life support device or system whose failure to perform can be reasonably expected to cause the failure of the life support device or system, or to affect its safety or effectiveness.

PRODUCT STATUS DEFINITIONS

Definition of Terms

Datasheet Identification	Product Status	Definition
Advance Information	Formative or In Design	This datasheet contains the design specifications for product development. Specifications may change in any manner without notice.
Preliminary	First Production	This datasheet contains preliminary data, and supplementary data will be published at a later date. Fairchild Semiconductor reserves the right to make changes at any time without notice in order to improve design.
No Identification Needed	Full Production	This datasheet contains final specifications. Fairchild Semiconductor reserves the right to make changes at any time without notice in order to improve design.
Obsolete	Not In Production	This datasheet contains specifications on a product that has been discontinued by Fairchild semiconductor. The datasheet is printed for reference information only.